

# Ferroelectric Thin Films for Tunable Microwave Applications

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## Technology Background

- ✗ Microwave technologies are the basis of modern wireless communication systems.
- ✗ Ferroelectrics are attractive for microwave devices due to:
  - strong electric field dependence of dielectric permittivity  $\epsilon'$
  - low microwave dielectric losses  $\tan \delta$
- ✗ Ferroelectric thin films technology offers advantages such as:
  - miniaturization of microwave components
  - low operating voltages
  - integration into electronic circuits

### Key functional property

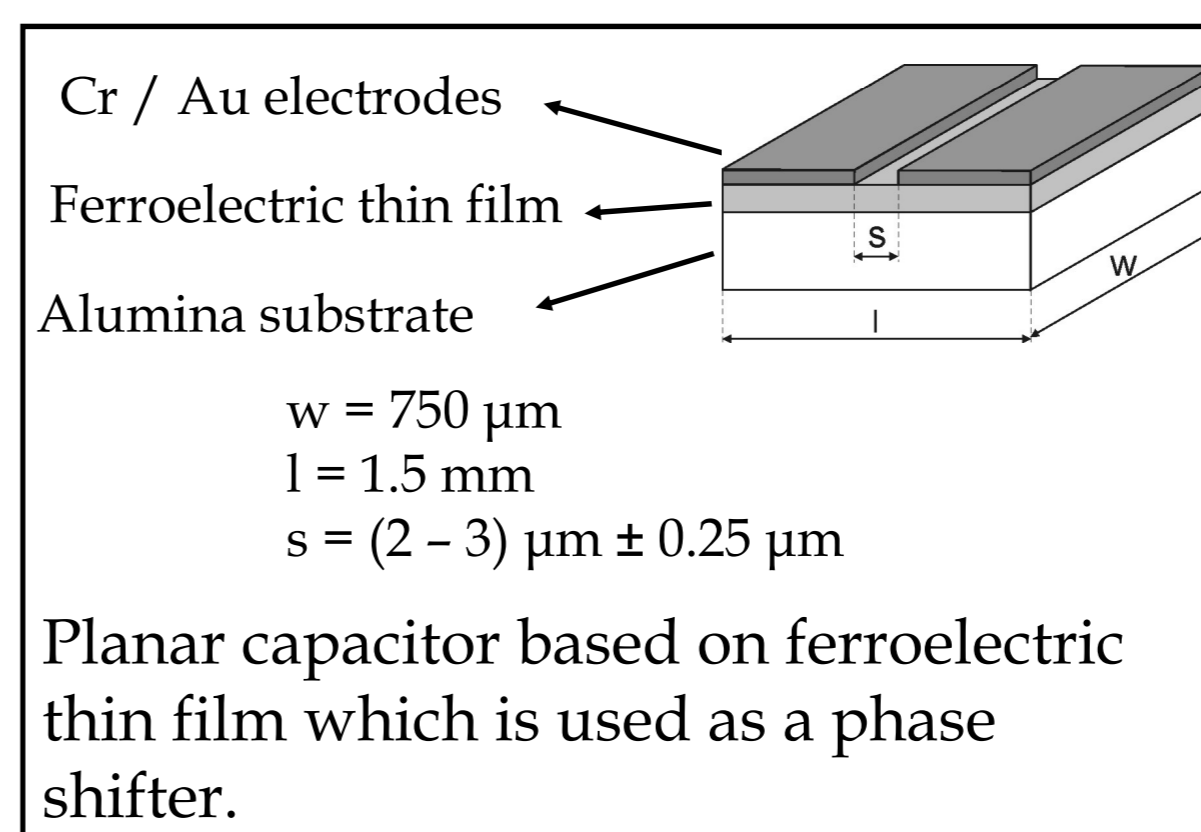
$$n_C = \frac{C(0)}{C(E_{\max})}$$

$n_C$ ...capacitance tunability

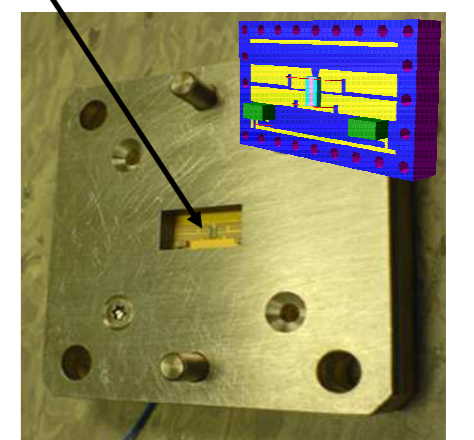
$C(0)$ ...capacitance at zero applied electric field

$C(E_{\max})$ ...capacitance at selected electric field

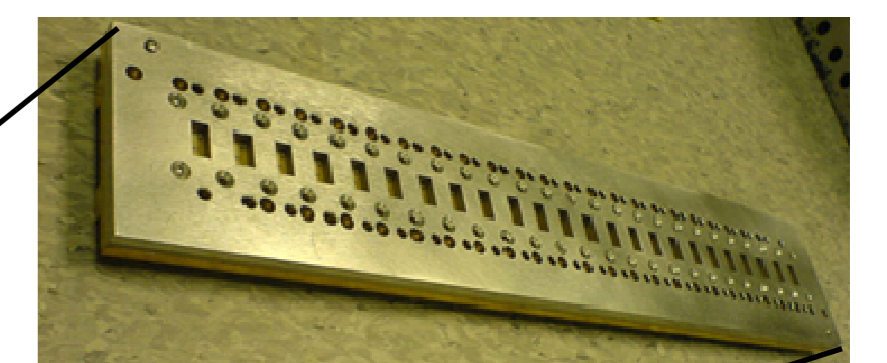
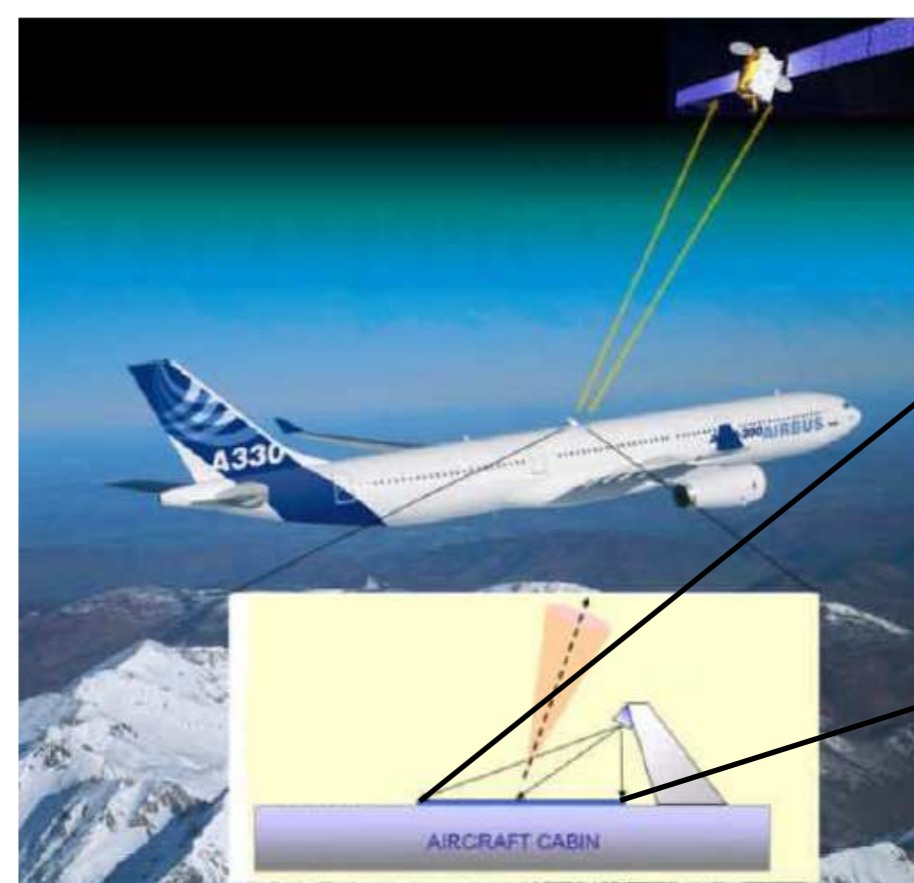
### Application: phase shifters in electronically steerable antennas\*



Planar capacitor



Phase shifter connected to the electronic circuit and mounted into metal housing.



1D phased array based on ferroelectric phase shifters

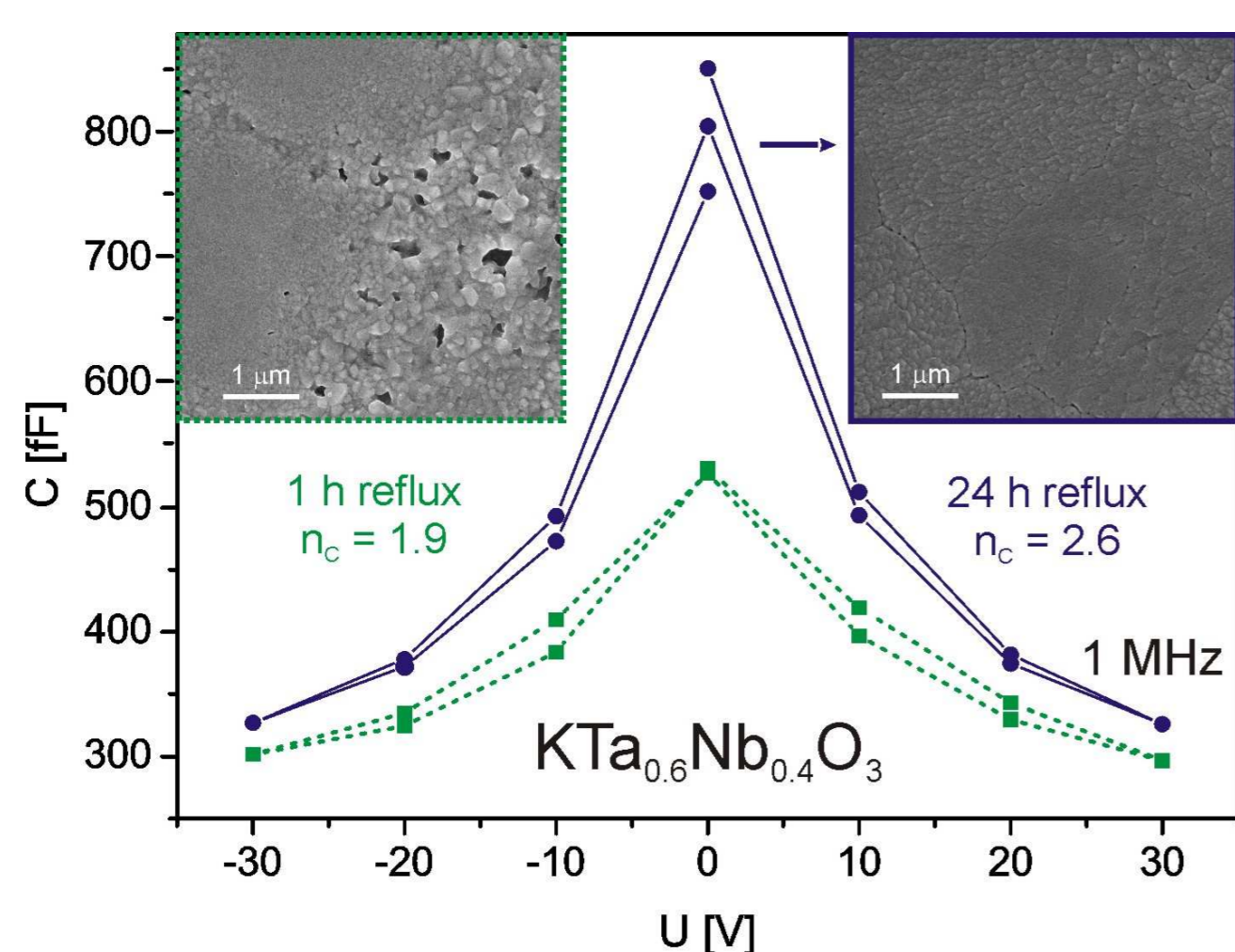
- ✗ Because of the geometry these antennas are convenient for aeronautical applications.

\*Developed in collaboration with Thales (France), EPFL (Switzerland), and HYB (Slovenia), RETINA (EC 6FP).

## Research Activities

Fast development of the communication systems stimulates the research of alternative materials.  $\text{K}(\text{Ta}, \text{Nb})\text{O}_3$  solid solution is a promising candidate, however, scarce literature data on preparation and dielectric properties exist.

- ✗ Homogeneous microstructure and strongly enhanced tunability ( $n_C$ ) were obtained by prolonged reflux time.



Films prepared from the 24 h-refluxed sols.

Composition	$\epsilon'$ (1 MHz)	$n_C$ (1 MHz)	$\epsilon'$ (~9.7 GHz)	$\tan \delta$ (~9.7 GHz)
$\text{KTa}_{0.6}\text{Nb}_{0.4}\text{O}_3$	2200	2.6	675	0.38
$\text{KTa}_{0.8}\text{Nb}_{0.2}\text{O}_3$	375	1.25	690	0.033
$\text{KTaO}_3$	190	1.01	220	0.017

- ✗ Dielectric properties are tuned through the Ta/Nb ratio.

### Chemical Solution Deposition of the Films

KOAc,  $\text{Ta}(\text{OEt})_5$ , and  $\text{Nb}(\text{OEt})_5$  were dissolved in 2-methoxyethanol.

Reactions were performed with different reflux times; by-products were removed by a distillation.

0.4 M sols were deposited on the alumina substrates by spin-coating.

App. 200 nm thick perovskite films were obtained after four sol depositions and heating at 900 °C for 15 min in an RTA furnace.

